



General Description

The MAX5972A provides a complete interface for a powered device (PD) to comply with the IEEE® 802.3af/at standard in a power-over-Ethernet (PoE) system. The MAX5972A provides the PD with a detection signature, classification signature, and an integrated isolation power switch with inrush current control. During the inrush period, the MAX5972A limits the current to less than 180mA before switching to the higher current limit (720mA to 880mA) when the isolation power MOSFET is fully enhanced. The device features an input UVLO with wide hysteresis and long deglitch time to compensate for twisted-pair cable resistive drop and to assure glitch-free transition during power-on/-off conditions. The MAX5972A can withstand up to 100V at the input.

The MAX5972A supports a 2-event classification method as specified in the IEEE 802.3at standard and provides a signal to indicate when probed by Type 2 power-sourcing equipment (PSE). The device detects the presence of a wall adapter power-source connection and allows a smooth switch over from the PoE power source to the wall power adapter.

The MAX5972A also provides a power-good (PG) signal, two-step current limit and foldback, overtemperature protection, and di/dt limit.

The MAX5972A is available in a 16-pin, 5mm x 5mm, TQFN power package. This device is rated over the -40°C to $+85^{\circ}\text{C}$ extended temperature range.

Applications

IEEE 802.3af/at-Powered Devices

IP Phones, Wireless Access Nodes, IP Security Cameras

WiMAX™ Base Station

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Features

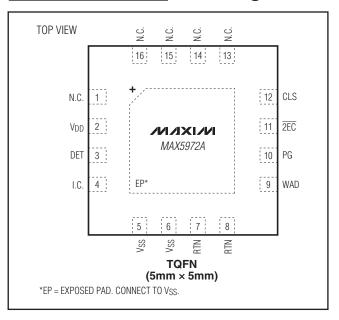
- ♦ IEEE 802.3af/at Compliant
- ♦ 2-Event Classification or an External Wall Adapter Indicator Output
- ♦ Simplified Wall Adapter Interface
- ♦ PoE Classification 0 to 5
- ♦ 100V Input Absolute Maximum Rating
- ♦ Inrush Current Limit of 180mA Maximum
- ♦ Current Limit During Normal Operation Between 720mA and 880mA
- **♦ Current Limit and Foldback**
- ♦ Legacy UVLO at 36V
- **♦** Overtemperature Protection
- ♦ Thermally Enhanced, 5mm x 5mm, 16-Pin TQFN

Ordering Information

PART	TEMP RANGE	PIN- PACKAGE	SLEEP MODE
MAX5972AETE+	-40°C to +85°C	16 TQFN-EP*	_

⁺Denotes a lead(Pb)-free/RoHS-compliant package.

Pin Configuration



Maxim Integrated Products 1

^{*}EP = Exposed pad.

ABSOLUTE MAXIMUM RATINGS

VDD to VSS0.3V to +100V	Pa
DET, RTN, WAD, PG, 2EC to V _{SS} 0.3V to +100V	
CLS to V _{SS} 0.3V to +6V	
Maximum Current on CLS (100ms maximum)100mA	O
Continuous Power Dissipation ($T_A = +70^{\circ}C$) (Note 1)	Ma
16-Pin TQFN (derate 28.6mW/°C above +70°C)	St
Multilayer Board2285.7mW	Le

Package Thermal Resistance (Note 2)	
θJA	35°C/W
θJC	2.7°C/W
Operating Temperature Range	40°C to +85°C
Maximum Junction Temperature	+150°C
Storage Temperature Range	65°C to +150°C
Lead Temperature (soldering, 10s)	+300°C

- Note 1: Maximum power dissipation is obtained using JEDEC JESD51-5 and JESD51-7 specifications.
- **Note 2:** Package thermal resistances were obtained using the method described in JEDEC specification JESD51-7, using a four-layer board. For detailed information on package thermal considerations, refer to www.maxim-ic.com/thermal-tutorial.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

ELECTRICAL CHARACTERISTICS

 $(V_{IN} = (V_{DD} - V_{SS}) = 48V, R_{DET} = 24.9k\Omega, R_{CLS} = 615\Omega. RTN, WAD, PG, and <math>\overline{2EC}$ unconnected, all voltages are referenced to V_{SS} , unless otherwise noted. $T_A = T_J = -40^{\circ}C$ to $+85^{\circ}C$, unless otherwise noted. Typical values are at $T_A = +25^{\circ}C$.) (Note 3)

PARAMETER	SYMBOL	CONDITIONS		MIN	TYP	MAX	UNITS
DETECTION MODE					-		
Input Offset Current	IOFFSET	$V_{IN} = 1.4V \text{ to } 10.$	1V (Note 4)			10	μΑ
Effective Differential Input Resistance	dR		10.1V with 1V step, AD = PG = $\overline{2EC}$ (Note 5)	23.95	25.00	25.50	kΩ
CLASSIFICATION MODE							
Classification Disable Threshold	VTH,CLS	V _{IN} rising (Note 6	5)	22.0	22.8	23.6	V
Classification Stability Time					0.2		ms
			Class 0, R _{CLS} = 615Ω	0		3.96	mA
		$V_{IN} = 12.5V \text{ to}$	Class 1, $R_{CLS} = 117\Omega$	9.12		11.88	
Classification Current	ICLASS	20.5V, V _{DD} = RTN = WAD =	Class 2, R _{CLS} = 66.5Ω	17.2		19.8	
Classification Current			Class 3, R _{CLS} = 43.7Ω	26.3		29.7	
		$PG = \overline{2EC}$	Class 4, R _{CLS} = 30.9Ω	36.4		43.6	
			Class 5, RCLS = 21.3Ω	52.7		63.3	
TYPE 2 (802.3at) CLASSIFIC	ATION MODE						
Mark Event Threshold	VTHM	V _{IN} falling		10.1	10.7	11.6	V
Hysteresis on Mark Event Threshold					0.84		V
Mark Event Current	IMARK	V_{IN} falling to enter mark event, $5.2V \le V_{IN}$ $\le 10.1V$		0.25		0.85	mA
Reset Event Threshold	VTHR	V _{IN} falling		2.8	4	5.2	V
POWER MODE							
VIN Supply Voltage Range						60	V
VIN Supply Current	IQ				0.27	0.55	mA

ELECTRICAL CHARACTERISTICS (continued)

 $(V_{IN} = (V_{DD} - V_{SS}) = 48V, R_{DET} = 24.9k\Omega, R_{CLS} = 615\Omega. R_{TN}, W_{AD}, P_{G}, and \overline{2EC}$ unconnected, all voltages are referenced to V_{SS}, unless otherwise noted. T_{A} = T_{J} = -40^{\circ}C to +85°C, unless otherwise noted. Typical values are at T_{A} = +25°C.) (Note 3)

PARAMETER	SYMBOL	CONDITIONS			TYP	MAX	UNITS
V _{IN} Turn-On Voltage	Von	V _{IN} rising	VIN rising		35.4	36.6	V
V _{IN} Turn-Off Voltage	Voff	V _{IN} falling	30			V	
V _{IN} Turn-On/-Off Hysteresis	VHYST_UVLO	(Note 7)		4.2			V
VIN Deglitch Time	tOFF_DLY	VIN falling from 40V to 2	0V (Note 8)	30	120		μs
Inrush to Operating Mode Delay	tDELAY	tDELAY = minimum PG of after entering into power		80	96	112	ms
Is alation Davis MOCETT			T _J = +25°C		0.7	1.1	
Isolation Power MOSFET On-Resistance	Ron_iso	IRTN = 600mA	TJ = +85°C		0.9	1.5	Ω
On resistance			T _J = +125°C		1.15		
RTN Leakage Current	IRTN_LKG	VRTN = 12.5V to 30V				10	μΑ
CURRENT LIMIT							
Inrush Current Limit	INRUSH	During initial turn-on per VRTN = 1.5V	During initial turn-on period, VRTN = 1.5V			180	mA
Current Limit During Normal Operation	ILIM	After inrush completed, VRTN = 1V	720	800	880	mA	
Foldback Threshold		V _{RTN} (Note 9)		13		16.5	V
LOGIC							
WAD Detection Threshold	Vwad-ref	VWAD rising, V _{IN} = 14V to 48V (referenced to RTN)		8	9	10	V
WAD Detection Threshold Hysteresis		VWAD falling, VRTN = 0V, VSS unconnected			0.725		V
WAD Input Current	lwad-lkg	VWAD = 10V (referenced	d to RTN)			3.5	μΑ
2EC Sink Current		V _{ZEC} = 3.5V (referenced to RTN), V _{SS} unconnected		1	1.5	2.25	mA
2EC Off-Leakage Current		V _{2EC} = 48V				1	μA
PG Sink Current		VRTN = 1.5V, VPG = 0.8 th period	125	230	375	μA	
PG Off-Leakage Current		V _{PG} = 60V				1	μΑ
THERMAL SHUTDOWN	*						
Thermal-Shutdown Threshold	T _{SD}	T _J rising			+140		°C
Thermal-Shutdown Hysteresis		T _J falling			+28		°C

- Note 3: This device is 100% production tested at $T_A = +25$ °C. Limits over temperature are guaranteed by design.
- Note 4: The input offset current is illustrated in Figure 1.
- Note 5: Effective differential input resistance is defined as the differential resistance between VDD and VSS. See Figure 1.
- Note 6: Classification current is turned off whenever the device is in power mode.
- Note 7: UVLO hysteresis is guaranteed by design, not production tested.
- Note 8: A 20V glitch on input voltage that takes VDD below Von shorter than or equal to toff_DLY does not cause the MAX5972A to exit power-on mode.
- **Note 9:** In power mode, current-limit foldback is used to reduce the power dissipation in the isolation MOSFET during an overload condition across VDD and RTN.

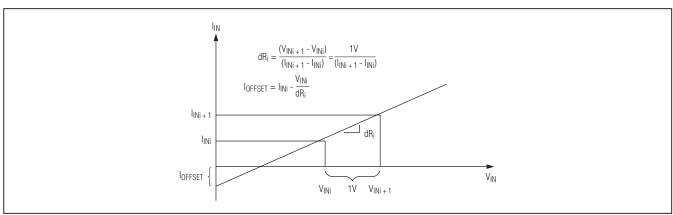
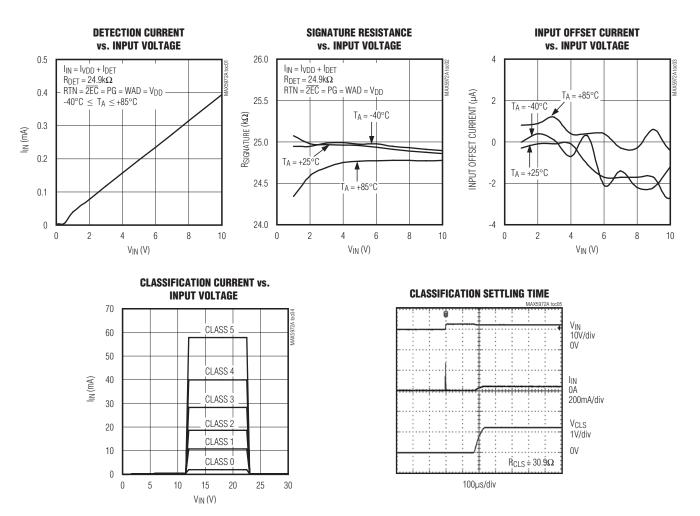


Figure 1. Effective Differential Input Resistance/Offset Current

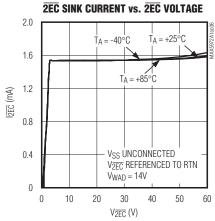
Typical Operating Characteristics

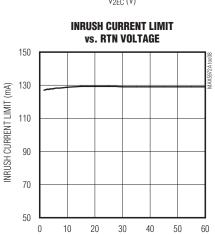
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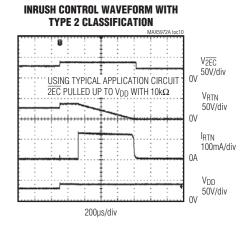
Typical Operating Characteristics (continued)

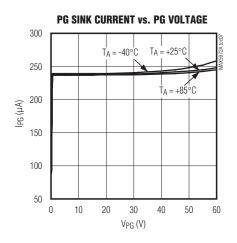
 $(V_{IN} = (V_{DD} - V_{SS}) = 54V, R_{DET} = 24.9k\Omega, R_{CLS} = 615\Omega, RTN, WAD, PG, and \overline{2EC}$ unconnected; all voltages are referenced to V_{SS} .)

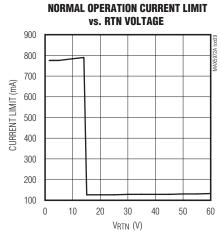


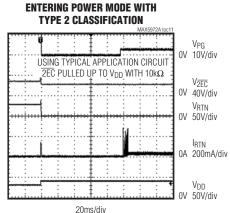


V_{RTN} (V)





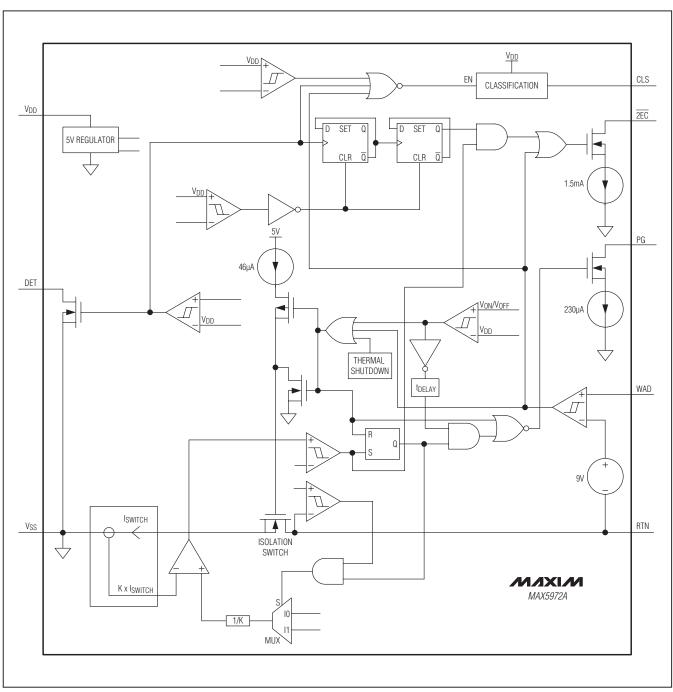




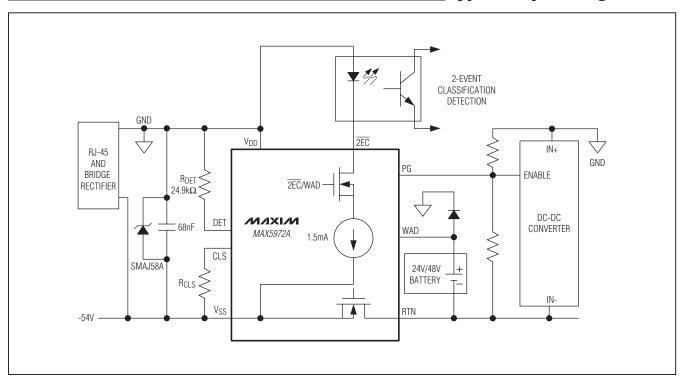
Pin Description

PIN	NAME	FUNCTION
1, 13–16	N.C.	No Connection. Not internally connected.
2	V _{DD}	Positive Supply Input. Connect a 68nF (min) bypass capacitor between VDD and VSS.
3	DET	Detection Resistor Input. Connect a signature resistor (RDET = 24.9k Ω) from DET to VDD.
4	I.C.	Internally Connected. Leave unconnected.
5, 6	Vss	Negative Supply Input. VSS connects to the source of the integrated isolation n-channel power MOSFET.
7, 8	RTN	Drain of Isolation MOSFET. RTN connects to the drain of the integrated isolation n-channel power MOSFET. Connect RTN to the downstream DC-DC converter ground as shown in the <i>Typical Application Circuit</i> .
9	WAD	Wall Power Adapter Detector Input. Wall adapter detection is enabled the moment VDD - VSS crosses the mark event threshold. Detection occurs when the voltage from WAD to RTN is greater than 9V. When a wall power adapter is present, the isolation n-channel power MOSFET turns off, $\overline{\text{2EC}}$ current sink turns on. Connect WAD directly to RTN when the wall power adapter or other auxiliary power source is not used.
10	PG	Open-Drain Power-Good Indicator Output. PG sinks 230µA to disable the downstream DC-DC converter while turning on the hot-swap MOSFET switch. PG current sink is disabled during detection, classification, and in the steady-state power mode. The PG current sink is turned on to disable the downstream DC-DC converter when the device is in sleep mode.
11	2EC	Active-Low 2-Event Classification Detect or Wall Adapter Detect Output. A 1.5mA current sink is enabled at \$\overline{2EC}\$ when a Type 2 PSE or a wall adapter is detected. When powered by a Type 2 PSE, the \$\overline{2EC}\$ current sink is enabled after the isolation MOSFET is fully on until VIN drops below the UVLO threshold. \$\overline{2EC}\$ is latched when powered by a Type 2 PSE until VIN drops below the reset threshold. \$\overline{2EC}\$ also asserts when a wall adapter supply, typically greater than 9V, is applied between WAD and RTN. \$\overline{2EC}\$ is not latched if asserted by WAD.
12	CLS	Classification Resistor Input. Connect a resistor (R _{CLS}) from CLS to V _{SS} to set the desired classification current. See the classification current specifications in the <i>Electrical Characteristics</i> table to find the resistor value for a particular PD classification.
_	EP	Exposed Pad. Do not use EP as an electrical connection to Vss. EP is internally connected to Vss through a resistive path and must be connected to Vss externally. To optimize power dissipation, solder the exposed pad to a large copper power plane.

Simplified Block Diagram



Typical Operating Circuit



Detailed Description

Operating Modes

Depending on the input voltage ($V_{IN} = V_{DD}$ - V_{SS}), the MAX5972A operates in four different modes: PD detection, PD classification, mark event, and PD power. The device enters PD detection mode when the input voltage is between 1.4V and 10.1V. The device enters PD classification mode when the input voltage is between 12.6V and 20V. The device enters PD power mode once the input voltage exceeds V_{ON} .

Detection Mode $(1.4V \le V_{IN} \le 10.1V)$

In detection mode, the power source equipment (PSE) applies two voltages on VIN in the range of 1.4V to 10.1V (1V step minimum) and then records the current measurements at the two points. The PSE then computes $\Delta V/\Delta I$ to ensure the presence of the 24.9k Ω signature resistor. Connect the signature resistor (RDET) from VDD to DET for proper signature detection. The MAX5972A pulls DET low

in detection mode. DET goes high impedance when the input voltage exceeds 12.5V. In detection mode, most of the MAX5972A internal circuitry is off and the offset current is less than $10\mu A$.

If the voltage applied to the PD is reversed, install protection diodes at the input terminal to prevent internal damage to the MAX5972A (see the *Typical Application Circuit*). Since the PSE uses a slope technique ($\Delta V/\Delta I$) to calculate the signature resistance, the DC offset due to the protection diodes is subtracted and does not affect the detection process.

Classification Mode (12.6 $V \le V_{IN} \le 20V$)

In the classification mode, the PSE classifies the PD based on the power consumption required by the PD. This allows the PSE to efficiently manage power distribution. Class 0 to 5 is defined as shown in Table 1. (The IEEE 802.3af/at standard defines only Class 0 to 4 and Class 5 for any special requirement.) An external resistor (RCLS) connected from CLS to VSS sets the classification current.

8 /V/XI/VI

Table 1. Setting Classification Current

CLASS	MAXIMUM POWER USED BY PD	R _{CLS} (Ω)	V _{IN} * (V)	CLASS CURRENT SEEN AT V _{IN} (mA)		CLASSIFICAT	2.3at PD ON CURRENT TION (mA)
	(W)			MIN	MAX	MIN	MAX
0	0.44 to 12.95	615	12.6 to 20	0	4	0	5
1	0.44 to 3.94	117	12.6 to 20	9	12	8	13
2	3.84 to 6.49	66.5	12.6 to 20	17	20	16	21
3	6.49 to 12.95	43.7	12.6 to 20	26	30	25	31
4	12.95 to 25.5	30.9	12.6 to 20	36	44	35	45
5	> 25.5	21.3	12.6 to 20	52	64	51	68

^{*}VIN is measured across the MAX5972A input VDD to VSS.

The PSE determines the class of a PD by applying a voltage at the PD input and measuring the current sourced out of the PSE. When the PSE applies a voltage between 12.6V and 20V, the MAX5972A exhibits a current characteristic with a value shown in Table 1. The PSE uses the classification current information to classify the power requirement of the PD. The classification current includes the current drawn by RCLS and the supply current of the MAX5972A so the total current drawn by the PD is within the IEEE 802.3af/at standard figures. The classification current is turned off whenever the device is in power mode.

2-Event Classification and Detection

During 2-event classification, a Type 2 PSE probes PD for classification twice. In the first classification event, the PSE presents an input voltage between 12.6V and 20.5V and the MAX5972A presents the programmed load ICLASS. The PSE then drops the probing voltage below the mark event threshold of 10.1V and the MAX5972A presents the mark current (IMARK). This sequence is repeated one more time.

When the MAX5972A is powered by a Type 2 PSE, the 2-event identification output $\overline{2EC}$ asserts low after the internal isolation n-channel MOSFET is fully turned on. $\overline{2EC}$ current sink is turned off when VDD goes below the UVLO threshold (VOFF) and turns on when VDD goes above the UVLO threshold (VON), unless VDD goes below VTHR to reset the latched output of the Type 2 PSE detection flag.

Alternatively, the $\overline{\text{2EC}}$ output also serves as a wall adapter detection output when the MAX5972A is powered by an external wall power adapter. See the *Wall Power Adapter Detection and Operation* section for more information.

Power Mode (Wake Mode)

The MAX5972A enters power mode when VIN rises above the undervoltage lockout threshold (VoN). When VIN rises above VoN, the MAX5972A turns on the internal n-channel isolation MOSFET to connect VSS to RTN with inrush current limit internally set to 135mA (typ). The isolation MOSFET is fully turned on when the voltage at RTN is near VSS and the inrush current is reduced below the inrush limit. Once the isolation MOSFET is fully turned on, the MAX5972A changes the current limit to 800mA. The open-drain power-good output (PG) remains low for a minimum of tDELAY until the power MOSFET fully turns on to keep the downstream DC-DC converter disabled during inrush.

Undervoltage Lockout

The MAX5972A operates up to a 60V supply voltage with a turn-on UVLO threshold (VON) at 35.4V and a turn-off UVLO threshold (VOFF) at 31V. When the input voltage is above VON, the MAX5972A enters power mode and the internal MOSFET is turned on. When the input voltage goes below VOFF for more than tOFF_DLY, the MOSFET turns off.

Power-Good Output

An open-drain output (PG) is used to allow disabling downstream DC-DC converter until the n-channel isolation MOSFET is fully turned on. PG is pulled low to VSS for a period of tDELAY and until the internal isolation MOSFET is fully turned on. The PG is also pulled low during sleep mode and coming out of thermal shutdown.

Thermal-Shutdown Protection

The MAX5972A includes thermal protection from excessive heating. If the junction temperature exceeds the thermal-shutdown threshold of +140°C, the MAX5972A

turns off the internal power MOSFET and $\overline{2EC}$ current sink. When the junction temperature falls below +112°C, the devices enter inrush mode and then return to power mode. Inrush mode ensures the downstream DC-DC converter is turned off as the internal power MOSFET is turned on.

Wall Power Adapter Detection and Operation

For applications where an auxiliary power source such as a wall power adapter is used to power the PD, the MAX5972A features wall power adapter detection. The MAX5972A gives highest priority to the WAD and smoothly switches the power supply to WAD when it is detected. Once the input voltage (VDD - VSS) exceeds the mark event threshold, the MAX5972A enables wall adapter detection. The wall power adapter is connected from WAD to RTN. The MAX5972A detects the wall power adapter when the voltage from WAD to RTN is greater than 9V. When a wall power adapter is detected, the internal n-channel isolation MOSFET turns off, $\overline{\rm 2EC}$ current sink turns on, and classification current is disabled if VIN is in the classification range.

Applications Information

Operation with 12V AdapterLayout Procedure

Careful PCB layout is critical to achieve high efficiency and low EMI. Follow these layout guidelines for optimum performance:

- 1) Place the input capacitor, classification resistor, and transient voltage suppressor as close as possible to the MAX5972A.
- 2) Use large SMT component pads for power dissipating devices such as the MAX5972A and the external diodes.
- 3) Use short and wide traces for high-power paths.
- 4) Use the MAX5972A evaluation kit layout as a reference.
- 5) Place enough vias in the pad for the EP of the MAX5972A so that heat generated inside can be effectively dissipated by the PCB copper. The recommended spacing for the vias is 1mm to 1.2mm pitch. The thermal vias should be plated (1oz copper) and have a small barrel diameter (0.3mm to 0.33mm).

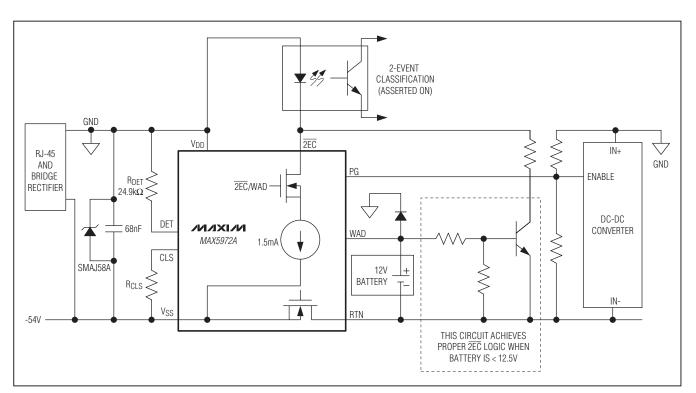
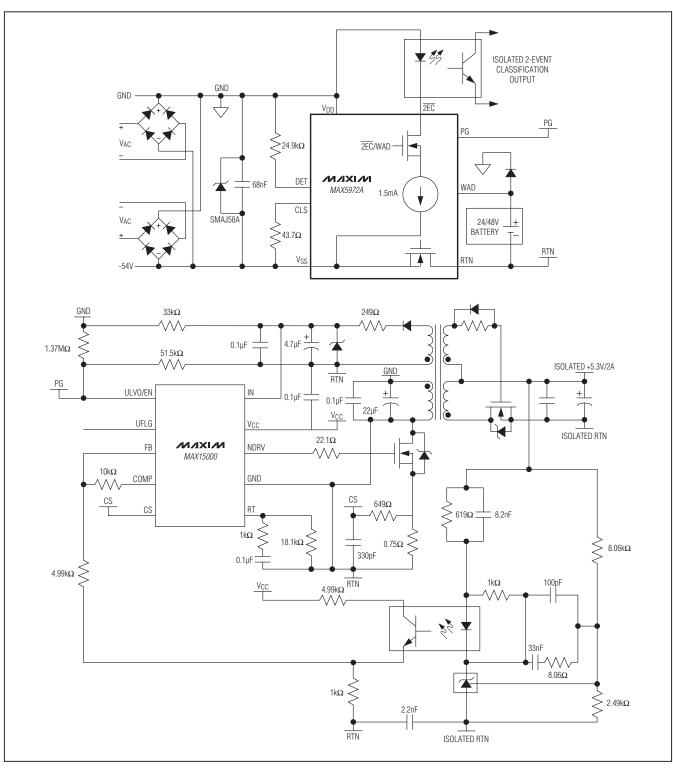


Figure 2. Typical Configuration When Using a 12V Wall Power Adapter

Typical Application Circuit



PROCESS: BICMOS

IEEE 802.3af/at-Compliant, Powered Device Interface Controller with Integrated Power MOSFET

_____Chip Information

_Package Information

For the latest package outline information and land patterns, go to www.maxim-ic.com/packages. Note that a "+", "#", or "-" in the package code indicates RoHS status only. Package drawings may show a different suffix character, but the drawing pertains to the package regardless of RoHS status.

PACKAGE TYPE	PACKAGE CODE	DOCUMENT NO.
16 TQFN-EP	T1655+4	21-0140

Revision History

REVISION NUMBER	REVISION DATE	DESCRIPTION	PAGES CHANGED
0	8/09	Initial release	_
1	2/10	Removed the MAX5972B from the data sheet.	1–13

Maxim cannot assume responsibility for use of any circuitry other than circuitry entirely embodied in a Maxim product. No circuit patent licenses are implied. Maxim reserves the right to change the circuitry and specifications without notice at any time.